SOT-23-3 PinConfiguration

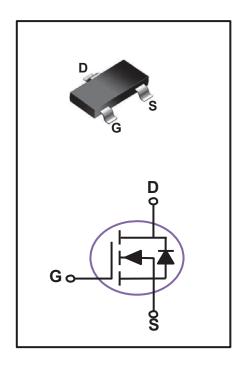
BVDSS	RDSON	ID
60V	75mΩ	3.2A

Features

- 60V,3.2A, $RDS(ON) = 75m\Omega@VGS = 10V$
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

Applications

- Motor Drive
- Power Tools
- LED Lighting



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current – Continuous (T _C =25°C)	1_	3.2	А
Drain Current – Continuous (T _C =100°C)	l _D	2	Α
Drain Current – Pulsed ¹	I _{DM}	12.8	А
Power Dissipation (T _C =25°C)	1.56		W
Power Dissipation – Derate above 25°C	P _D	0.012	W/°C
Storage Temperature Range	T _{STG}	-50 to 150	°C
Operating Junction Temperature Range	TJ	-50 to 150	°C

Thermal Characteristics

Parameter	Symbol	Тур.	Max.	Unit
Thermal Resistance Junction to ambient	$R_{\theta JA}$		80	°C/W

60VN-ChannelMOSFETS

LDN6912S

MOSFETELECTRICAL CHARACTERISTICS T_A=25c unless otherwise specified

Off Characteristics

Parameter	Symbol	ymbol Conditions		Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS} V _{GS} =0V , I _D =250uA		60			V
BV _{DSS} Temperature Coefficient	△BV _{DSS} /△T _J	△BV _{DSS} /△T _J Reference to 25°C , I _D =1mA		0.05		V/°C
Dunin Course Legland Commant		V _{DS} =60V , V _{GS} =0V , T _J =25°C			1	uA
Drain-Source Leakage Current	I _{DSS}	V _{DS} =48V , V _{GS} =0V , T _J =125°C			10	uA
Gate-Source Leakage Current	I _{GSS}	V_{GS} =±20V , V_{DS} =0V			±100	nA

On Characteristics

Static Drain-Source On-Resistance	В	V _{GS} =10V , I _D =6A		60	75	mΩ
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =4.5V , I _D =3A		70	90	mΩ
Gate Threshold Voltage	$V_{GS(th)}$	\/=\/	1.2	1.8	2.5	V
V _{GS(th)} Temperature Coefficient	$\triangle V_{GS(th)}$	$V_{GS}=V_{DS}$, I_D =250uA		-5		mV/°C
Forward Transconductance	gfs	V _{DS} =10V , I _D =3A		7		S

Dynamic and switching Characteristics

Total Gate Charge ^{2, 3}	Qg		 9.3	14	
Gate-Source Charge ^{2, 3}	Q _{gs}	V _{DS} =48V , V _{GS} =10V , I _D =6A	 2.1	4	nC
Gate-Drain Charge ^{2, 3}	Q_gd	1	 1.8	4	
Turn-On Delay Time ^{2, 3}	$T_{d(on)}$		 2.9	6	
Rise Time ^{2,3}	Tr	V_{DD} =30V , V_{GS} =10V ,	 9.5	18	
Turn-Off Delay Time ^{2 , 3}	$T_{d(off)}$	R _G =3.3Ω I _D =1A	 18.4	35	ns
Fall Time ^{2,3}	T _f]	 5.3	10	
Input Capacitance	C _{iss}		 500	725	
Output Capacitance	C _{oss}	V_{DS} =15V , V_{GS} =0V , F=1MHz	 45	65	pF
Reverse Transfer Capacitance	C _{rss}		 16	30	
Gate resistance	Rg	V _{GS} =0V, V _{DS} =0V, F=1MHz	 2	4	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Parameter	Symbol Conditions		Min.	Тур.	Max.	Unit
Continuous Source Current	Is	\/-=\/-=0\/			3.2	Α
Pulsed Source Current	I _{SM}	V _G =V _D =0V , Force Current			6.4	Α
Diode Forward Voltage	V _{SD}	V _{GS} =0V , I _S =1A , T _J =25°C			1	V
Reverse Recovery Time ²	t _{rr}	V _G s=30V,I _S =1A , dI/dt=100A/ μs		23.2		ns
Reverse Recovery Charge ²	Q _{rr}	T _J =25°C		14.3		nC

Note:

- 1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
- 2. The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%.
- 3. Essentially independent of operating temperature.

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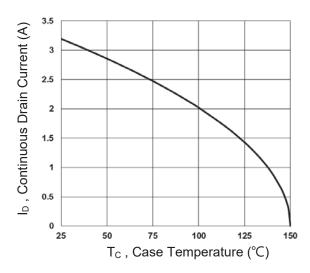


Fig.1 Continuous Drain Current vs. T_c

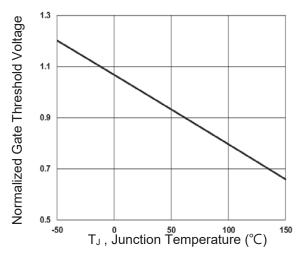


Fig.3 Normalized V_{th} vs. T_J

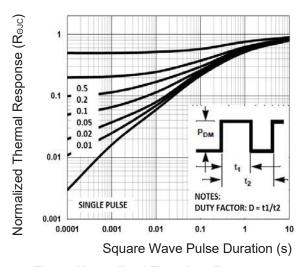


Fig.5 Normalized Transient Response

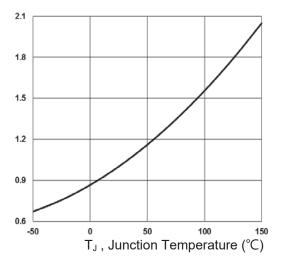


Fig.2 Normalized RDSON vs. T_J

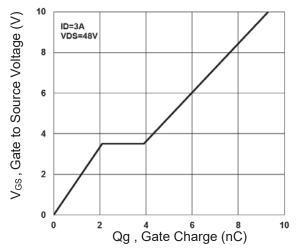


Fig.4 Gate Charge Waveform

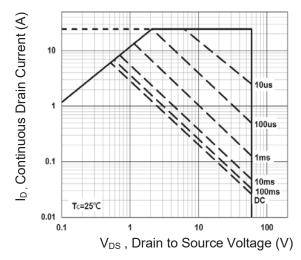


Fig.6 Maximum Safe Operation Area

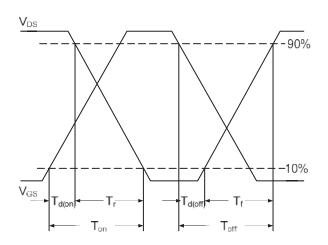


Fig.7 Switching Time Waveform

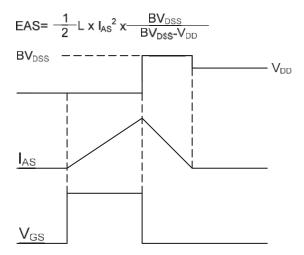
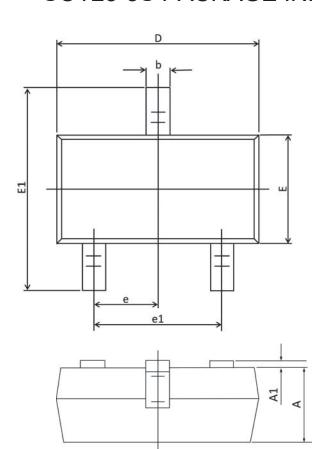
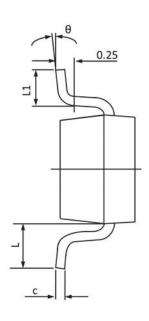


Fig.8 EAS Waveform



SOT23-3S PACKAGE INFORMATION





Cymahal	Dimensions In		Dimensio	ns In Inches
Symbol	Min	Max	Min	Max
Α	0.900	1.000	0.03	0.039
A 1	0.000	0.100	0.00	0.004
b	0.300	0.500	0.012	0.020
С	0.090	0.110	0.003	0.004
D	2.800	3.000	0.110	0.118
Е	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.950	0.950 TYP.		TYP.
е	1.800	2.000	0.071	0.079
L	0.550	REF.	0.022	REF.
L1	0.300	0.500	0.012	0.020
θ	1°	7°	1°	7°